Docket No. 240800US2S DIV
IN RE APPLICATION OF: Norihisa ARAI
SERIAL NO: 10/670,529
FILED: September 26, 2003
FOR: METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE INCLUDING PROCESS FOR IMPLANTING IMPURITIES INTO SUBSTRATE VIA MOS TRANSISTOR GATE ELECTRODE AND GATE INSULATION FILM

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:
Transmitted herewith is an amendment in the above-identified application.

■ No additional fee is required
☐ Small entity status of this application under 37 C.F.R. §1.9 and §1.27 is claimed.
☐ Additional documents filed herewith:

The Fee has been calculated as shown below:

CLAIMS	CLAIMS REMAINING		HIGHEST NUMBER PREVIOUSLY PAID	NO. EXTRA CLAIMS	RATE	CALCULATIONS
TOTAL	15	MINUS	20	0	x $50 =	$0.00
INDEPENDENT	3	MINUS	3	0	x $200 =	$0.00
		☐ MULTIPLE DEPENDENT CLAIMS			+ $360 =	$0.00
		TOTAL OF ABOVE CALCULATIONS				$0.00
		☐ Reduction by 50% for filing by Small Entity				$0.00
		☐ Recordation of Assignment			+ $40 =	$0.00
					TOTAL	$0.00

☐ A check in the amount of **$0.00** is attached.

☐ Credit card payment form is attached to cover the fees in the amount of **$0.00**

■ Please charge any additional Fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit Account No. 15-0030. A duplicate copy of this sheet is enclosed.

■ If these papers are not considered timely filed by the Patent and Trademark Office, then a petition is hereby made under 37 C.F.R. §1.136, and any additional fees required under 37 C.F.R. §1.136 for any necessary extension of time may be charged to Deposit Account No. 15-0030. A duplicate copy of this sheet is enclosed.

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IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF	:
NORIHISA ARAI	: EXAMINER: ROSE, KIESHA L.
SERIAL NO: 10/670,529	:
FILED: SEPTEMBER 26, 2003	: GROUP ART UNIT: 2822
FOR: METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE INCLUDING PROCESS FOR IMPLANTING IMPURITIES INTO SUBSTRATE VIA MOS TRANSISTOR GATE ELECTRODE AND GATE INSULATION FILM	:

AMENDMENT

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

In response to the Office Action dated October 5, 2004, please amend the above-identified application as follows:

Amendments to the Specification begin on page 2 of this paper.

Amendments to the Claims are reflected in the listing of claims which begins on page 3 of this paper.

Remarks/Arguments begin on page 7 of this paper.